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CONFIRMATION NO. 2226

SERIAL NUMBER 10/817,035	FILING DATE 04/05/2004  RULE	CLASS 257	GROUP ART UNIT 2811	ATTORNEY DOCKET NO. 61352-075		
<b>APPLICANTS</b>  Nobuyuki Otsuka, Kawanishi-shi, JAPAN;  Koichi Mizuno, Nara-shi, JAPAN; Shigeo Yoshii, Osaka, JAPAN; Asamira Suzuki, Osaka, JAPAN;  ** CONTINUING DATA ***** This application is a CON of PCT/JP03/13747 10/28/2003  ** FOREIGN APPLICATIONS ***** JAPAN 2002-318190 10/31/2002 JAPAN 2002-313902 10/29/2002  IF REQUIRED, FOREIGN FILING LICENSE GRANTED ** 06/23/2004						
Foreign Priority claimed 35 USC 119 (a-d) conditions met Verified and Acknowledged		<input type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance Examiner's Signature Initials	STATE OR COUNTRY JAPAN	SHEETS DRAWING 14	TOTAL CLAIMS 19	INDEPENDENT CLAIMS 2
<b>ADDRESS</b> 20277 MCDERMOTT WILL & EMERY LLP 600 13TH STREET, N.W. WASHINGTON, DC 20005-3096						
<b>TITLE</b> GALLIUM INDIUM NITRIDE ARSENIDE BASED EPITAXIAL WAFER, A HETERO FIELD EFFECT TRANSISTOR USING THE WAFER, AND A METHOD OF FABRICATING THE HETERO FIELD EFFECT TRANSISTOR						
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